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removed from the metal target then coat the wafer surface. It is also possible to utilize CVD techniques in which the titanium is formed from the reaction of TiCl₄ with hydrogen (H₂). In any event, the deposition material should get down into the High Aspect Ratio opening, and reach the bottom surface of the opening or via 20. A collimator may be used to direct the atoms straight down, for better coverage on the contacts.

In the Claims:

Please replace the claims with the respective amended claims below.

AI
Amend B1

1. (Amended) A method for removing polymer etch residue from an etched opening in a silicon wafer device, comprising:

forming an opening in an insulating layer, wherein a polymer etch residue remains within said opening after the opening forming step; and

contacting said opening with a plasma generated from ammonia gas to remove said polymer etch residue.

AI Amend B1

6. (Amended) The method of claim 2, wherein said contacting is done at a temperature within the range of about 250 - 500° C.

Amend B1

29. (Amended) A method of forming a contact opening in a semiconductor device, comprising:

a) etching a contact opening in an insulative layer in said device down to a polysilicon element of said device; and

b) cleaning etch residue from said etched opening by contacting said opening with ammonia gas in the form of a plasma.
